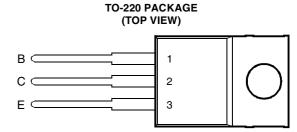
BOURNS®

- Designed for Complementary Use with BDT60, BDT60A, BDT60B and BDT60C
- 50 W at 25°C Case Temperature
- 4 A Continuous Collector Current
- Minimum h_{FE} of 750 at 1.5V, 3 A





MDTRACA

This series is obsolete and not recommended for new designs.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BDT61		60		
Collector-base voltage ($I_E = 0$)	BDT61A	V	80	V	
Collector-base voltage (IE = 0)	BDT61B	СВО	100	V	
	BDT61C		120		
	BDT61		60	_	
Collector-emitter voltage (I _B = 0)	BDT61A	V	80	٧	
	BDT61B	V _{CEO}	100		
	BDT61C		120		
Emitter-base voltage		V _{EBO}	5	V	
Continuous collector current		I _C	4	Α	
Continuous base current		I _B	0.1	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)			50	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 2)			2	W	
Operating junction temperature range		P _{tot}	-65 to +150	°C	
Storage temperature range		T _{stg}	-65 to +150	°C	
Operating free-air temperature range		T _A	-65 to +150	°C	

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.

2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS				MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 30 mA	I _B = 0	(see Note 3)	BDT61 BDT61A BDT61B BDT61C	60 80 100 120			V
I _{CEO}	Collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 40 \text{ V}$ $V_{CE} = 50 \text{ V}$ $V_{CE} = 60 \text{ V}$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BDT61 BDT61A BDT61B BDT61C			0.5 0.5 0.5 0.5	mA
Ісво	Collector cut-off current		I _E = 0	$T_{C} = 150^{\circ}\text{C}$ $T_{C} = 150^{\circ}\text{C}$ $T_{C} = 150^{\circ}\text{C}$ $T_{C} = 150^{\circ}\text{C}$	BDT61 BDT61A BDT61B BDT61C BDT61 BDT61A BDT61B BDT61C			0.2 0.2 0.2 0.2 2.0 2.0 2.0 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	I _C = 0					5	mA
h _{FE}	Forward current transfer ratio	V _{CE} = 3 V	I _C = 1.5 A	(see Notes 3 and	14)	750			
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = 6 mA	I _C = 1.5 A	(see Notes 3 and	14)			2.5	V
V _{BE(on)}	Base-emitter voltage	V _{CE} = 3 V	I _C = 1.5 A	(see Notes 3 and	14)			2.5	V
V _{EC}	Parallel diode forward voltage	I _E = 1.5 A	$I_B = 0$					2	٧

NOTES: 3. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			2.5	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = 2 A	$I_{B(on)} = 8 \text{ mA}$	$I_{B(off)} = -8 \text{ mA}$		1		μs
t _{off}	Turn-off time	$V_{BE(off)} = -5 V$	$R_L = 20 \Omega$	$t_p = 20 \mu s, dc \le 2\%$		4.5		μs

 $[\]begin{tabular}{ll} \dagger Voltage and current values shown are nominal; exact values vary slightly with transistor parameters. \end{tabular}$

^{4.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN vs **COLLECTOR CURRENT** TCS110AD 20000 $T_c = -40^{\circ}C$ T_c = 25°C 10000 T_c = 100°C h_{FE} - Typical DC Current Gain 1000 3 V = 300 μs, duty cycle < 2% 100 0.5 1.0 5.0 I_c - Collector Current - A

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE

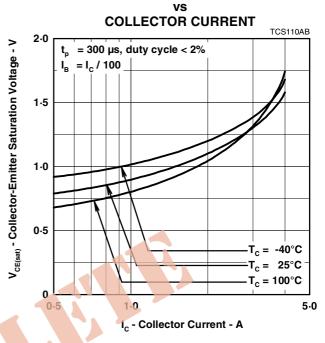
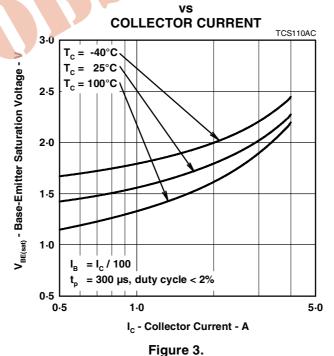


Figure 2.

BASE-EMITTER SATURATION VOLTAGE



PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

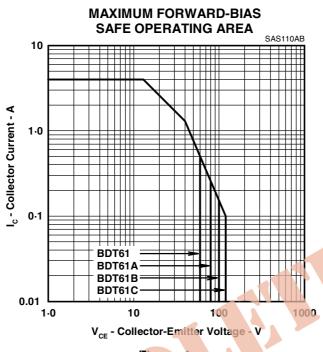


Figure 4

THERMAL INFORMATION

MAXIMUM POWER DISSIPATION vs CASE TEMPERATURE

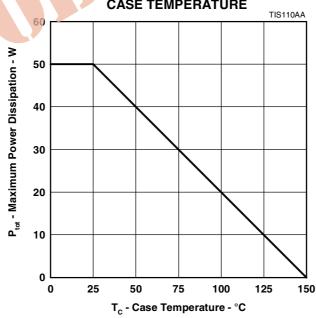


Figure 5.